L Number	Hits	Search Text	DB	Time stamp
•	2	6251488.pn. 6288442.pn.	USPAT;	2004/07/22 09:11
			US-PGPUB	
- }	7196	438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls.	USPAT;	2004/07/22 09:16
		438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls.	US-PGPUB	
		427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls.		
		427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.		
- i	1943	(438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls.	USPAT;	2004/07/22 09:25
i		438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls.	US-PGPUB	
		427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls.		
į		427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.)		
		and (aerosol spray\$6 nanoparticle)		2004/07/22 00.26
-	663	((438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls.	USPAT;	2004/07/22 09:26
		438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls.	US-PGPUB	
		427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls.		
		427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.)		
		and (aerosol spray\$6 nanoparticle)) and (integrated		
		semiconductor memory cell)	LICDATE	2004/07/22 00:22
-	453	(((438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls.	USPAT;	2004/07/22 09:23
		438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls.	US-PGPUB	
İ		427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls.		
		427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.)		
		and (aerosol spray\$6 nanoparticle)) and (integrated		
	Ó	semiconductor memory cell)) and (via hole opening plug		
	222	seed)	LICDAT	2004/07/22 00:24
-	239	(((438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls.	USPAT;	2004/07/22 09:24
		438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls.	US-PGPUB	
		427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls.		
		427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.)		
1		and (aerosol spray\$6 nanoparticle)) and (integrated		
		semiconductor memory cell)) and ((via hole opening plug		
	750	seed) with (conduct\$6 copper cu silver ag gold au))	LICDAT.	2004/07/22 09:28
-	759	(438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls.	USPAT; US-PGPUB	2004/07/22 09.20
		438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls.	03-2020	
		427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls.		
		427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.) and ((aerosol spray\$6 nanoparticle) same (conduct\$6		
	222	copper cu silver ag gold au)) ((438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls.	USPAT;	2004/07/22 12:17
-	323	438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls.	US-PGPUB	2007/07/22 12.17
		427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls.	OS FGFOD	
		427/123.ccis. 427/191.ccis. 427/192.ccis. 427/230.ccis. 427/230.ccis. 427/383.1.ccis. 427/422.ccis. 427/455.ccis. 427/597.ccis.)		
		and ((aerosol spray\$6 nanoparticle) same (conduct\$6		
		copper cu silver ag gold au))) and (integrated		
		semiconductor memory cell)		
_	465	(438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls.	USPAT;	2004/07/22 09:26
-	403	438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls.	US-PGPUB	200 1/07/22 03.20
		427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls.	03 1 01 00	
		427/123.ccis. 427/191.ccis. 427/192.ccis. 427/230.ccis. 427/230.ccis. 427/383.1.ccis. 427/422.ccis. 427/455.ccis. 427/597.ccis.)		
		and ((aerosol spray\$6 nanoparticle) with (conduct\$6 copper		
		cu silver ag gold au))		
	192	((438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls.	USPAT;	2004/07/22 09:30
	172	438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls.	US-PGPUB	200 1,07,22 05.50
		427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls.	33 1 3, 05	
		427/123.ccis. 427/191.ccis. 427/192.ccis. 427/230.ccis. 427/383.1.ccis. 427/422.ccis. 427/455.ccis. 427/597.ccis.)		
		and ((aerosol spray\$6 nanoparticle) with (conduct\$6 copper		
		cu silver ag gold au))) and (integrated semiconductor		
		memory cell)	1	
	6486	(aerosol spray\$6 nanoparticle) same (conduct\$6 copper cu	USPAT;	2004/07/22 09:33
	טטדט	silver ag gold au) same (via hole opening plug seed)	US-PGPUB	200 1,07,22 05.55
_	1403	(aerosol spray\$6 nanoparticle) with (conduct\$6 copper cu	USPAT;	2004/07/22 09:29
1	1403	silver ag gold au) with (via hole opening plug seed)	US-PGPUB	200 1,01,22 05.25

-	1288	(aerosol spray\$6) with (conduct\$6 copper cu silver ag gold au) with (via hole opening plug seed)	USPAT; US-PGPUB	2004/07/22 09:29
-	657	((aerosol spray\$6 nanoparticle) with (conduct\$6 copper cu silver ag gold au) with (via hole opening plug seed)) and (integrated semiconductor memory cell)	USPAT; US-PGPUB	2004/07/22 09:34
-	520	((aerosol spray\$6 nanoparticle) same (conduct\$6 copper cu silver ag gold au) same (via hole opening plug seed)) same	USPAT; US-PGPUB	2004/07/22 09:31
-	274	(integrated semiconductor memory cell) ((aerosol spray\$6 nanoparticle) same (conduct\$6 copper cu silver ag gold au) same (via hole opening plug seed)) same	USPAT; US-PGPUB	2004/07/22 09:31
-	7426	(memory cell) (aerosol spray\$6 nanoparticle) and (conduct\$6 copper cu silver ag gold au) and (via hole opening plug seed)	EPO; JPO; DERWENT;	2004/07/22 09:34
-	509	((aerosol spray\$6 nanoparticle) and (conduct\$6 copper cu silver ag gold au) and (via hole opening plug seed)) and	IBM_TDB EPO; JPO; DERWENT;	2004/07/22 09:35
-	1641	(integrated semiconductor memory cell) (aerosol spray\$6 nanoparticle) same (conduct\$6 copper cu silver ag gold au) same (via hole opening plug seed)	IBM_TDB EPO; JPO; DERWENT;	2004/07/22 09:35
-	44	(438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls. 438/678.ccls. 438/686.ccls.) and (427/97.ccls. 427/110.ccls. 427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls.	IBM_TDB USPAT; US-PGPUB	2004/07/22 09:35
-	85	427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.) ((aerosol spray\$6 nanoparticle) with (conduct\$6 copper cu silver ag gold au) with (via hole opening plug seed)) same	USPAT; US-PGPUB	2004/07/22 10:02
-	5	(integrated semiconductor memory cell) ("4389973" "4582731" "4714047" "4848273"	USPAT	2004/07/22 11:37
_	10	"5328078").PN. 5529634.URPN.	USPAT	2004/07/22 11:40
-	153	((aerosol spray\$6 nanoparticle) same (conduct\$6 copper cu silver ag gold au) same (via hole opening plug seed)) and (integrated semiconductor memory cell)	EPO; JPO; DERWENT; IBM_TDB	2004/07/22 11:54
-	110	((438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls. 438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls. 427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls. 427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.) and ((aerosol spray\$6 nanoparticle) same (conduct\$6 copper cu silver ag gold au))) and (((integrated adj circuit) ic semiconductor memory cell) same (via hole opening plug seed))	USPAT; US-PGPUB	2004/07/22 16:00
-	268	(maskless adj mesoscale adj2 (materials deposition)) m3d "m.sup.3d" "m.sup.3 d"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 16:04
-	158	((maskless adj mesoscale adj2 (materials deposition)) m3d "m.sup.3d" "m.sup.3 d") and (via plug semiconductor ic (integrated adj circuit))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 16:05
-	102	((maskless adj mesoscale adj2 (materials deposition)) m3d "m.sup.3d" "m.sup.3 d") and (via plug semiconductor ic (integrated adj circuit)) and (conduct\$6 copper cu silver ag gold au)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/22 17:08
-	1	1998jp-0340264.ap,prai.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/07/22 17:33
-	10	(memory adj (cell circuit array)) same (column with row with (decoder address)) same (sensing adj (circuit amplifier)) same (via plug)	DERWENT USPAT; US-PGPUB	2004/07/22 17:40
		I A A A A A A A A A A A A A A A A A A A		·

Search History 7/23/04 11:24:25 AM Page 2

-	2	((memory adj (cell circuit array)) same (column with row	USPAT;	2004/07/22 17:45
}		with (decoder address)) same (sensing adj (circuit	US-PGPUB	
		amplifier))) and (plug same ((bit adj line) (word adj line)		
	_	wordline bitline))		0004/07/00 47 47
-	5	((memory adj (cell circuit array)) same (column with row	USPAT;	2004/07/22 17:47
	1	with (decoder address)) same (sensing adj (circuit	US-PGPUB	
ŀ	<u> </u>	amplifier))) and (interconnect\$6 same ((bit adj line) (word		
		adj line) wordline bitline))		0004/07/00 47 40
-	2619	(memory adj (cell circuit array)) same plug	USPAT;	2004/07/22 17:48
		<u>.</u>	US-PGPUB	
-	1444	(memory adj (cell circuit array)) with plug	USPAT;	2004/07/22 17:48
			US-PGPUB	
-	370	(memory adj (cell circuit array)) same (plug with dielectric)	USPAT;	2004/07/22 17:49
į.			US-PGPUB	
-	158	(memory adj (cell circuit array)) with (plug with dielectric)	USPAT;	2004/07/22 17:49
1			US-PGPUB	
-	358	((memory adj (cell circuit array)) same (plug with	USPAT;	2004/07/22 17:52
		dielectric)) and (438/\$.ccls. 257/\$.ccls.)	US-PGPUB	
-	153	((memory adj (cell circuit array)) with (plug with dielectric))	USPAT;	2004/07/22 17:53
		and (438/\$.ccls. 257/\$.ccls.)	US-PGPUB	